

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0224DA uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = 200V, I_D = 24A$ $R_{DS(ON)} < 80m\Omega @ V_{GS} = 10V$ (Typ:62m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

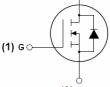
100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0224DA	NCE0224DA	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	200	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	١ _D	24	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	17	А
Pulsed Drain Current	I _{DM}	100	А
Maximum Power Dissipation	PD	150	W
Single pulse avalanche energy (Note 5)	E _{AS}	250	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C



(2) D

Schematic diagram

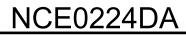


Marking and pin assignment









Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1	°C/W
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Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·	·	•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	200	220	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·	·	•			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1	1.5	2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A	-	62	80	mΩ
Forward Transconductance	g fs	V _{DS} =50V,I _D =15A	30	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}			4200		PF
Output Capacitance	C _{oss}	V _{DS} =25V,V _{GS} =0V,		163		PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz		75		PF
Switching Characteristics (Note 4)						•
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	tr	V _{DD} =100V,I _D =15A	-	18	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =2.5 Ω	-	22	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg)/ <u>400)/</u> 1 45A		60		nC
Gate-Source Charge	Q _{gs}	V_{DS} =100V,I _D =15A,		19		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V		17		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =11A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S	-	-	-	24	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 15A	-	90	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	300	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

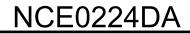
4. Guaranteed by design, not subject to production

5. EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=100V,V_G=10V,L=0.5mH,Rg=25 Ω



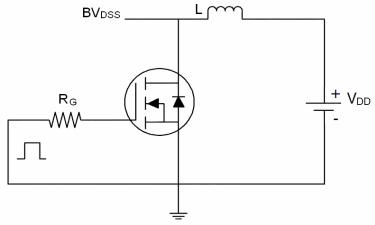
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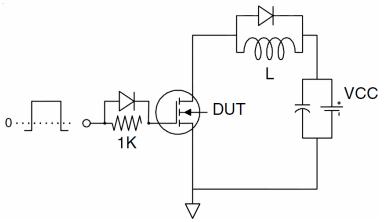


Test circuit

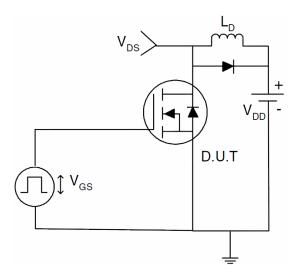
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit

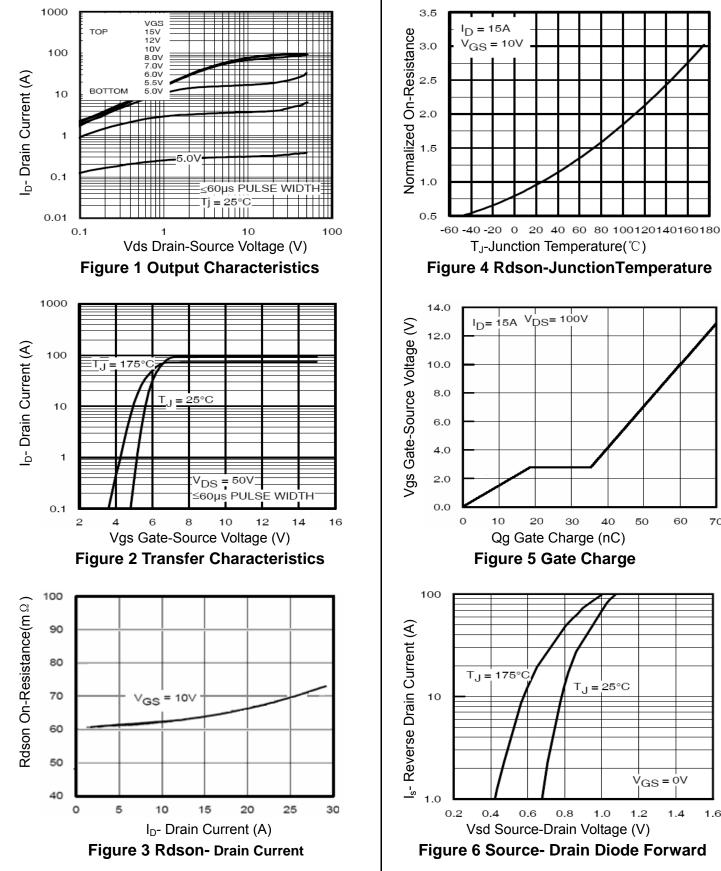


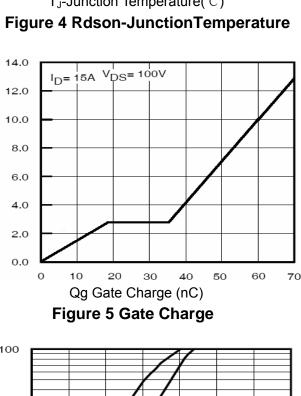




NCE0224DA

Typical Electrical and Thermal Characteristics (Curves)





1.6

V_{GS} = OV

1.4

1.2

1.0



75

100 125 150 175

V_{DS}=V_{GS} ID=250µA

100

PDN

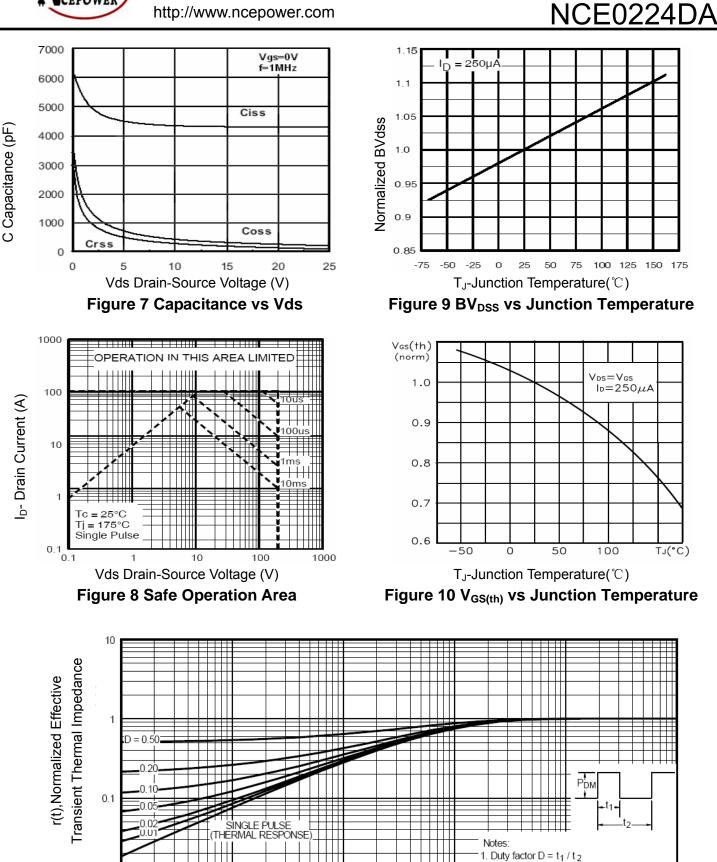
2. Peak TJ = P DM X ZthJC + TC

0.1

TJ(°C)



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Square Wave Pluse Duration(sec)

0.01



0.01

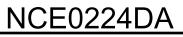
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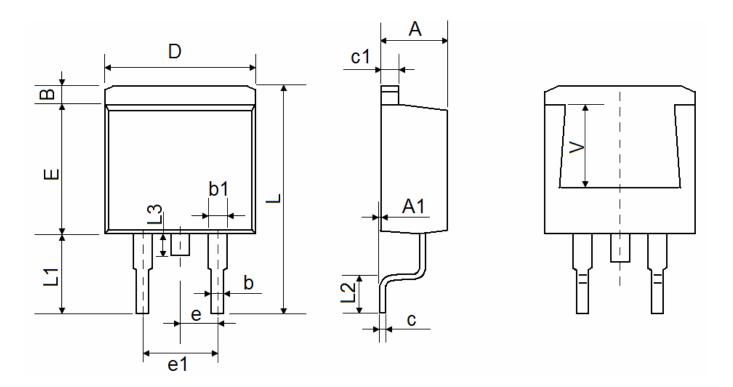
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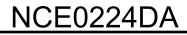
TO-263-2L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
с	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.600) REF	0.220 REF		







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